





P-CHANNEL ENHANCEMENT MODE FIELD EFFECT TRANSISTOR

Features

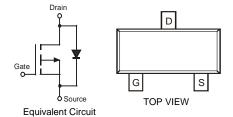
- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Lead, Halogen and Antimony Free, RoHS Compliant "Green" Device (Notes 3 and 4)
- · Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: SOT-23
- Case Material: UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Terminals: Solderable per MIL-STD-202, Method 208
- Lead Free Plating (Matte Tin Finish).
- Terminal Connections: See Diagram
- Marking Information: See Page 3
- Ordering Information: See Page 3
- Weight: 0.008 grams (approximate)



SOT-23



Maximum Ratings @T_A = 25°C unless otherwise specified

Characteristic		Symbol	Value	Units
Drain-Source Voltage		V_{DSS}	-50	V
Drain-Gate Voltage $R_{GS} \le 20K\Omega$		V_{DGR}	-50	V
Gate-Source Voltage	Continuous	V_{GSS}	±20	V
Drain Current (Note 1)	Continuous	I _D	-130	mA

Thermal Characteristics @TA = 25°C unless otherwise specified

Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 1)	P _d	300	mW
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	417	°C/W
Operating and Storage Temperature Range	T _j , T _{STG}	-55 to +150	°C

Electrical Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition		
OFF CHARACTERISTICS (Note 2)								
Drain-Source Breakdown Voltage	BV _{DSS}	-50	-	_	٧	$V_{GS} = 0V, I_D = -250\mu A$		
			_	-15	μΑ	$V_{DS} = -50V$, $V_{GS} = 0V$, $T_{J} = 25^{\circ}C$		
Zero Gate Voltage Drain Current	I_{DSS}	_	_	-60	μΑ	$V_{DS} = -50V$, $V_{GS} = 0V$, $T_{J} = 125$ °C		
		—	_	-100	nA	$V_{DS} = -25V$, $V_{GS} = 0V$, $T_{J} = 25^{\circ}C$		
Gate-Body Leakage	I _{GSS}			±10	nΑ	$V_{GS} = \pm 20V, V_{DS} = 0V$		
ON CHARACTERISTICS (Note 2)								
Gate Threshold Voltage	$V_{GS(th)}$	-0.8	_	-2.0	V	$V_{DS} = V_{GS}$, $I_D = -1mA$		
Static Drain-Source On-Resistance	R _{DS} (ON)	_		10	Ω	$V_{GS} = -5V, I_D = -0.100A$		
Forward Transconductance	g FS	0.05	_	_	S	$V_{DS} = -25V, I_{D} = -0.1A$		
DYNAMIC CHARACTERISTICS								
Input Capacitance	C _{iss}	_	_	45	рF			
Output Capacitance	Coss	_	_	25	рF	$V_{DS} = -25V, V_{GS} = 0V, f = 1.0MHz$		
Reverse Transfer Capacitance	C _{rss}	_	_	12	рF			
SWITCHING CHARACTERISTICS								
Turn-On Delay Time	t _{D(ON)}	_	10	_	ns	$V_{DD} = -30V$, $I_{D} = -0.27A$,		
Turn-Off Delay Time	t _{D(OFF)}	_	18	_	ns	$R_{GEN} = 50\Omega$, $V_{GS} = -10V$		

Notes:

- 1. Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch; pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.
- 2. Short duration pulse test used to minimize self-heating effect.
- 3. No purposefully added lead. Halogen and Antimony Free.
- Product manufactured with Data Code V9 (week 33, 2008) and newer are built with Green Molding Compound. Product manufactured prior to Date Code V9 are built with Non-Green Molding Compound and may contain Halogens or Sb₂O₃ Fire Retardants.



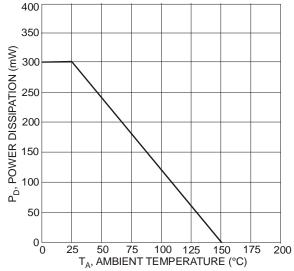
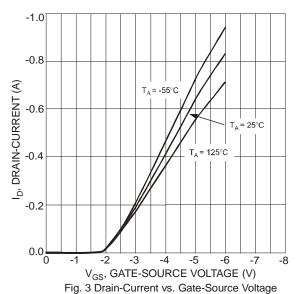


Fig. 1 Max Power Dissipation vs. Ambient Temperature



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V_{GS} = -10V
I_D = -0.13A

(C)

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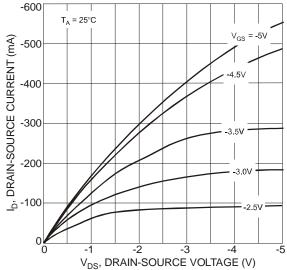


Fig. 2 Drain-Source Current vs. Drain-Source Voltage

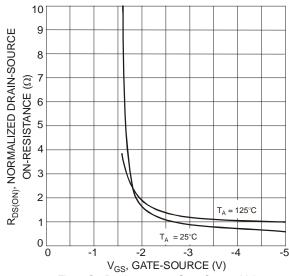
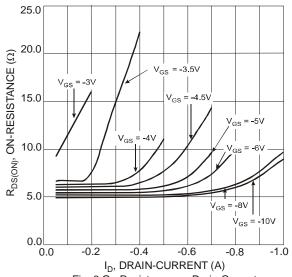


Fig. 4 On-Resistance vs. Gate-Source Voltage



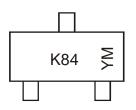


Ordering Information (Note 5)

Part Number	Case	Packaging
BSS84-7-F	SOT-23	3000/Tape & Reel

Notes: 5. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

Marking Information

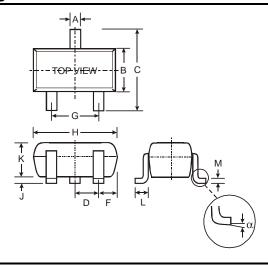


K84 = Product Type Marking Code YM = Date Code Marking Y = Year ex: N = 2002 M = Month ex: 9 = September

Date Code Key

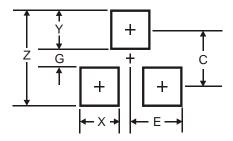
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Year	1998	1999	2000	2001	2002	2003	2004	2005	2006	2007	2008	2009	2010	2011	2012
Code	J	K	L	М	N	Р	R	S	Т	U	V	W	Χ	Υ	Z
Month	Jan	Fel	b	Mar	Apr	May	Ju	n	Jul	Aug	Sep	Oc	t I	Nov	Dec
Code	1	2		3	4	5	6	i	7	8	9	0		N	D

Package Outline Dimensions



SOT-23					
Dim	Min	Max			
Α	0.37	0.51			
В	1.20	1.40			
C	2.30	2.50			
D	0.89	1.03			
F	0.45	0.60			
G	1.78	2.05			
Η	2.80	3.00			
7	0.013	0.10			
K	0.903	1.10			
┙	0.45	0.61			
M	0.085	0.180			
α	0°	8°			
All Dimensions in mm					

Suggested Pad Layout



Dimensions	Value (in mm)
Z	3.4
G	0.7
Х	0.9
Υ	1.4
С	2.0
E	0.9

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